Title (en)

SEMICONDUCTOR MEMORY DEVICE AND METHOD FOR THE PRODUCTION THEREOF

Title (de)

HALBLEITERSPEICHEREINRICHTUNG SOWIE VERFAHREN ZU DEREN HERSTELLUNG

Title (fr)

MEMOIRE A SEMI-CONDUCTEUR ET SON PROCEDE DE PRODUCTION

Publication

EP 1565949 A2 20050824 (DE)

Application

EP 03788820 A 20031124

Priority

- DE 0303885 W 20031124
- DE 10255117 A 20021126

Abstract (en)

[origin: WO2004049440A2] Disclosed are a semiconductor memory device (1) having a memory effect due to phase transformation and a method for the production thereof, according to which a hollow space arrangement (H) comprising at least one hollow space (H1, H2) that is disposed near the respective memory element (E) is provided for each memory element (E) in a semiconductor substrate (20) such that thermal coupling of the respective memory element (E) to the surroundings thereof is embodied in a reduced manner by lowering thermal conductivity between the memory element (E) and the surroundings.

IPC 1-7

H01L 45/00

IPC 8 full level

H01L 27/24 (2006.01); H01L 45/00 (2006.01)

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